

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16245FT

Low-Voltage 16-Bit Bus Transceiver with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16245FT is a high-performance CMOS 16-bit bus transceiver. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

This 16-bit bus transceiver is controlled by direction control (DIR) inputs and output enable (\overline{OE}) inputs which are common to each byte. It can be used as two 8-bit transceivers or one 16-bit transceiver. The direction of data transmission is determined by the level of the DIR inputs. The \overline{OE} inputs can be used to disable the device so that the busses are effectively isolated.

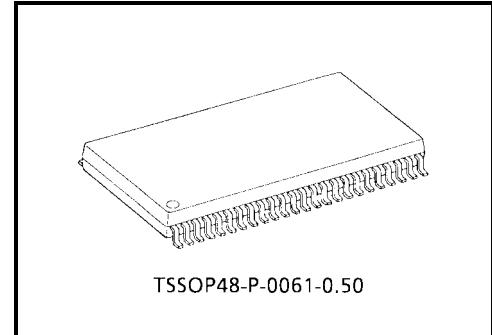
All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 2.5$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 - : $t_{pd} = 3.0$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 - : $t_{pd} = 5.0$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 - : $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 - : $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
 - : Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

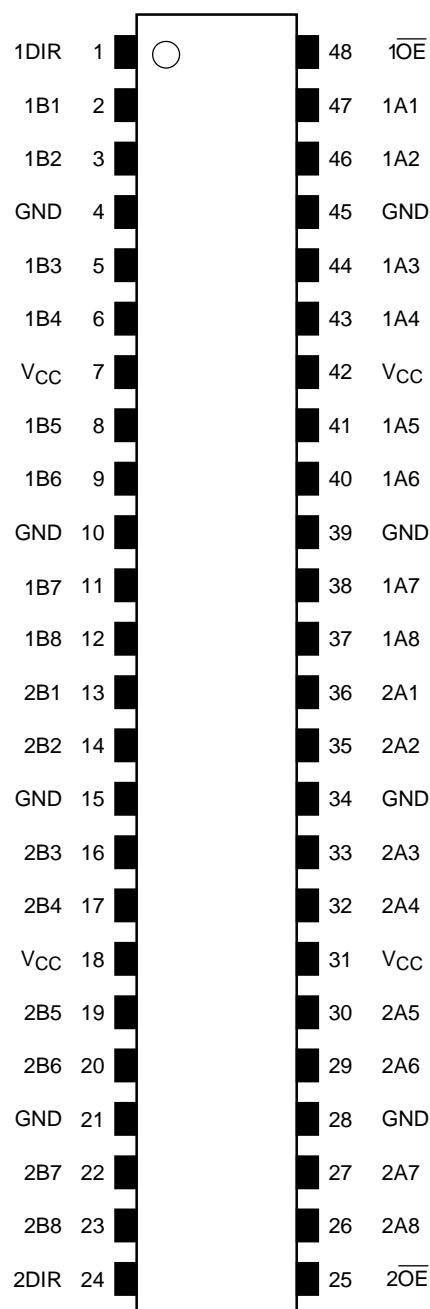
Note 1: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

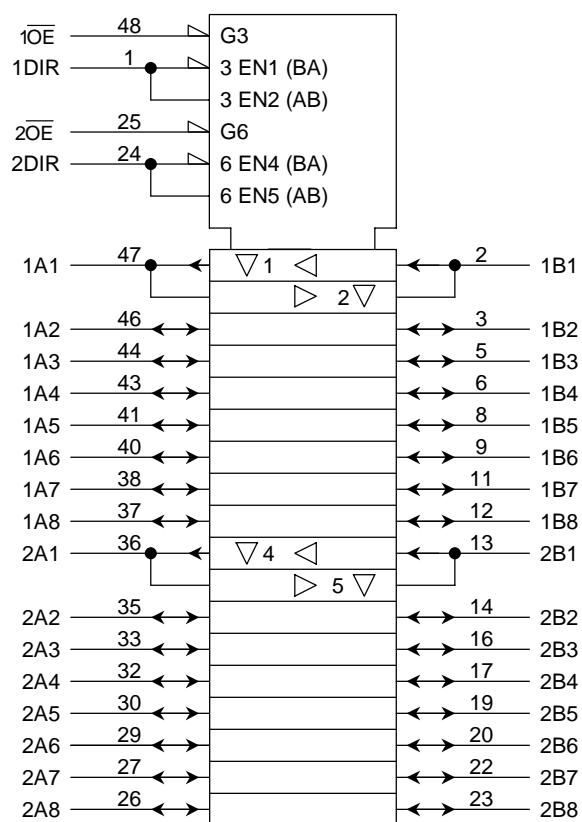


Weight: 0.25 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



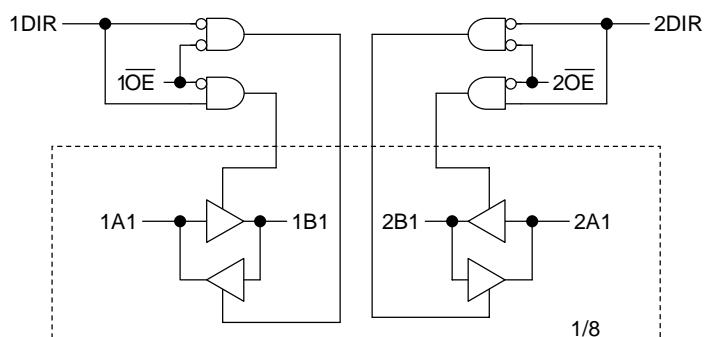
Truth Table

Inputs		Function		Outputs
$\overline{1OE}$	1DIR	Bus 1A1-1A8	Bus 1B1-1B8	
L	L	Output	Input	A = B
L	H	Input	Output	B = A
H	X	Z	Z	Z

Inputs		Function		Outputs
$\overline{2OE}$	2DIR	Bus 2A1-2A8	Bus 2B1-2B8	
L	L	Output	Input	A = B
L	H	Input	Output	B = A
H	X	Z	Z	Z

X: Don't care

Z: High impedance

System Diagram

1/8

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	−0.5 to 4.6	V
DC input voltage (DIR, \overline{OE})	V _{IN}	−0.5 to 4.6	V
DC bus I/O voltage	V _{I/O}	−0.5 to 4.6 (Note 2)	V
		−0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	−50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	−65 to 150	°C

Note 2: OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 5)	
Input voltage (DIR, \overline{OE})	V _{IN}	−0.3 to 3.6	V
Bus I/O voltage	V _{I/O}	0 to 3.6 (Note 6)	V
		0 to V _{CC} (Note 7)	
Output current	I _{OH} /I _{OL}	±24 (Note 8)	mA
		±18 (Note 9)	
		±6 (Note 10)	
Operating temperature	T _{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 11)	ns/V

Note 5: Data retention only

Note 6: OFF state

Note 7: High or low state

Note 8: V_{CC} = 3.0 to 3.6 V

Note 9: V_{CC} = 2.3 to 2.7 V

Note 10: V_{CC} = 1.8 V

Note 11: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		V _{IH}	—		2.7 to 3.6	2.0	—	
	L-level	V _{IL}	—	—	2.7 to 3.6	—	0.8	V	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -12 mA	2.7	2.2	—		
				I _{OH} = -18 mA	3.0	2.4	—		
				I _{OH} = -24 mA	3.0	2.2	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2		
				I _{OL} = 12 mA	2.7	—	0.4		
				I _{OL} = 18 mA	3.0	—	0.4		
				I _{OL} = 24 mA	3.0	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	±20.0		
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750		

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		V _{IH}	—		2.3 to 2.7	1.6	—	
	L-level	V _{IL}	—	—	2.3 to 2.7	—	0.7	V	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.3	2.0	—		
				I _{OH} = -12 mA	2.3	1.8	—		
				I _{OH} = -18 mA	2.3	1.7	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2		
				I _{OL} = 12 mA	2.3	—	0.4		
				I _{OL} = 18 mA	2.3	—	0.6		
				I _{OL} = 24 mA	2.3 to 2.7	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.3 to 2.7	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	±20.0		

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \text{ V} \leq V_{CC} < 2.3 \text{ V}$)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—		1.8 to 2.3	$0.7 \times V_{CC}$	—	V	
	L-level	V_{IL}	—		1.8 to 2.3	—	$0.2 \times V_{CC}$		
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.8	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 \text{ mA}$	1.8	1.4	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.8	—	0.2		
				$I_{OL} = 6 \text{ mA}$	1.8	—	0.3		
Input leakage current		I_{IN}	$V_{IN} = 0$ to 3.6 V		1.8	—	± 5.0	μA	
3-state output OFF state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	—	± 10.0	μA	
Power-off leakage current		I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	—	± 20.0		

AC Characteristics ($T_a = -40$ to 85°C , input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Propagation delay time	t_{PLH} t_{PHL}	Figure 1, Figure 2			1.8	1.5	5.0	ns
					2.5 ± 0.2	1.0	3.0	
					3.3 ± 0.3	0.8	2.5	
3-state output enable time	t_{PZL} t_{PZH}	Figure 1, Figure 3			1.8	1.5	7.5	ns
					2.5 ± 0.2	1.0	4.9	
					3.3 ± 0.3	0.8	3.8	
3-state output disable time	t_{PLZ} t_{PHZ}	Figure 1, Figure 3			1.8	1.5	5.5	ns
					2.5 ± 0.2	1.0	4.2	
					3.3 ± 0.3	0.8	3.7	
Output to output skew	t_{osLH} t_{osHL}	(Note 12)			1.8	—	0.5	ns
					2.5 ± 0.2	—	0.5	
					3.3 ± 0.3	—	0.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note 12: Parameter guaranteed by design.

$$(tosLH = |t_{PLHm} - t_{PLHn}|, tosHL = |t_{PHLm} - t_{PHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 13)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 13)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 13)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 13)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 13)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 13)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 13)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 13)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 13)	3.3	2.2	

Note 13: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note 14)	1.8, 2.5, 3.3	20	pF

Note 14: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC} (\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$$

AC Test Circuit

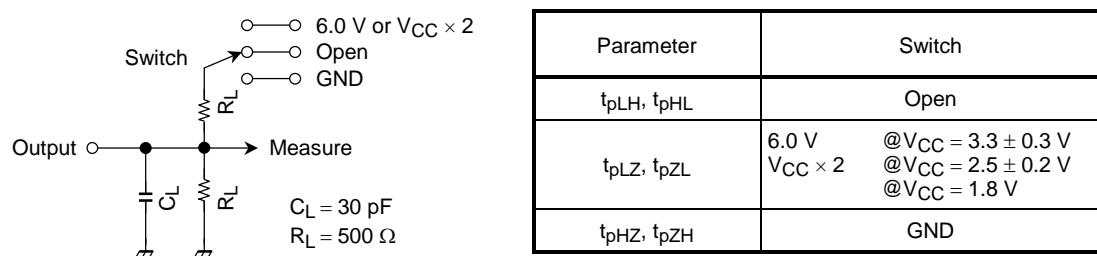
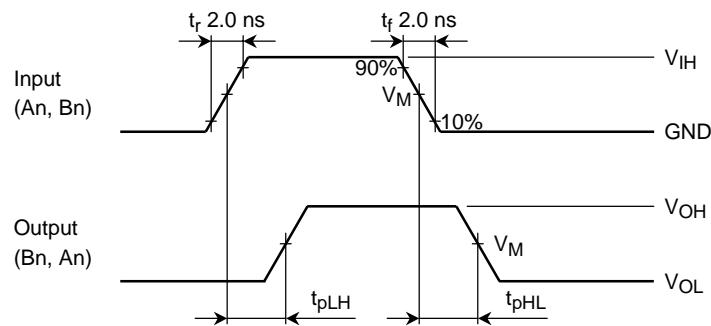
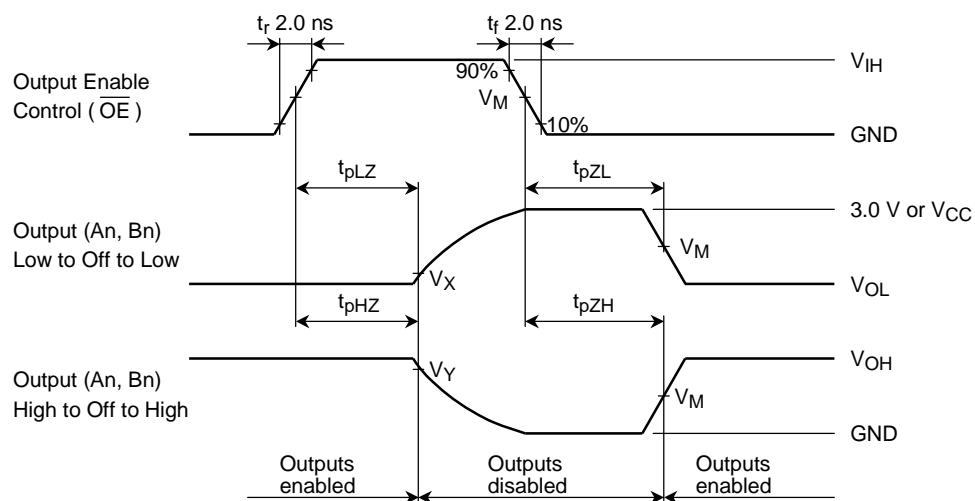


Figure 1

AC Waveform

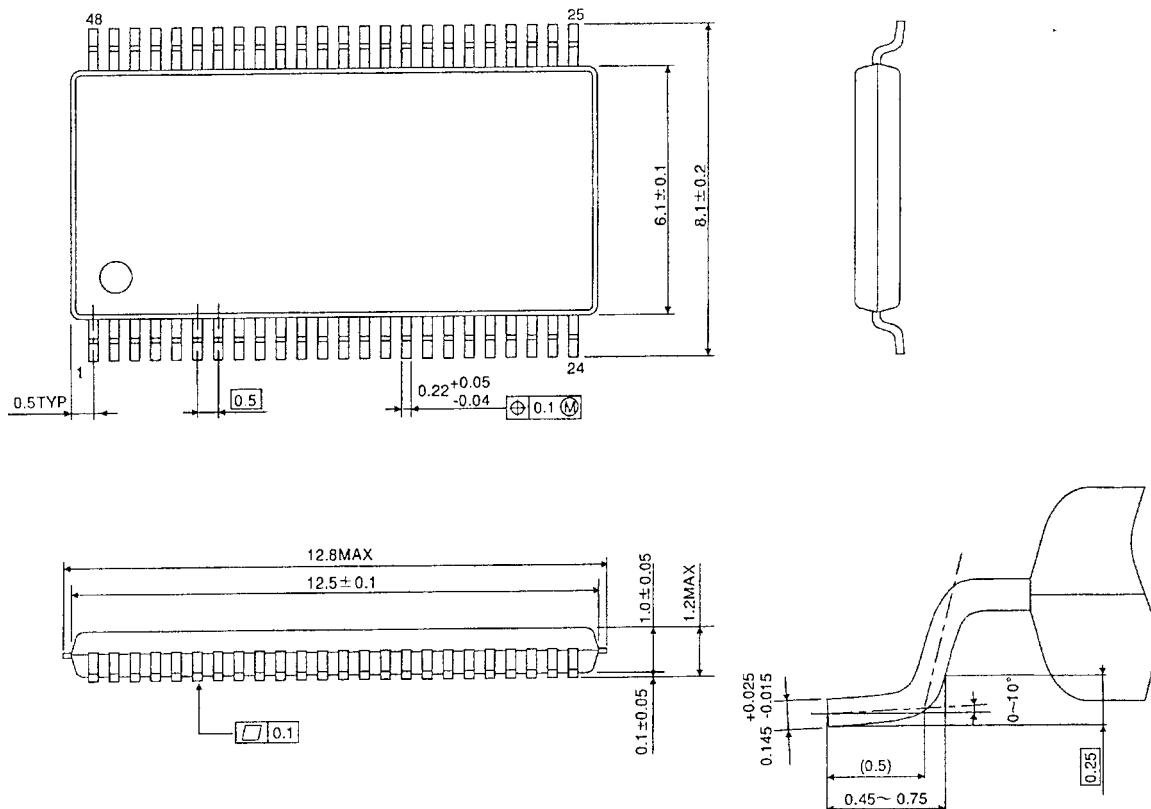
Figure 2 t_{pLH}, t_{pHL} Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

Package Dimensions

TSSOP48-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

RESTRICTIONS ON PRODUCT USE

000707EBA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.